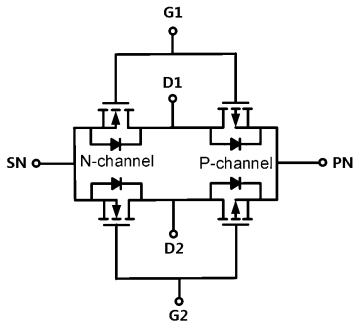
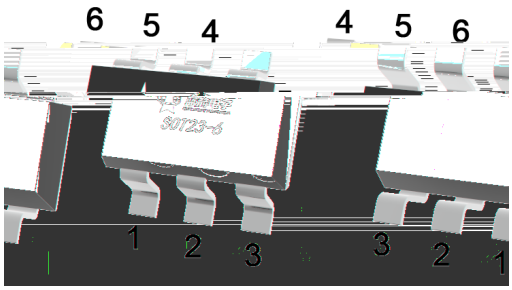
N channel	P-channel
V_{DS}(V)=30V	V_{DS}(V)=-30V
I_D=2.7A	I_D=-2.6A
$R_{DS(ON)}$@10V<80m (TYP. 66 m)	$R_{DS(ON)}$@-10V<95 m (TYP. 75 m)
$R_{DS(ON)}$@4.5V<130m (TYP. 95 m)	$R_{DS(ON)}$@-4.5V<150 m (TYP. 88 m)
HF Product.	

PWM applications,Load switch.



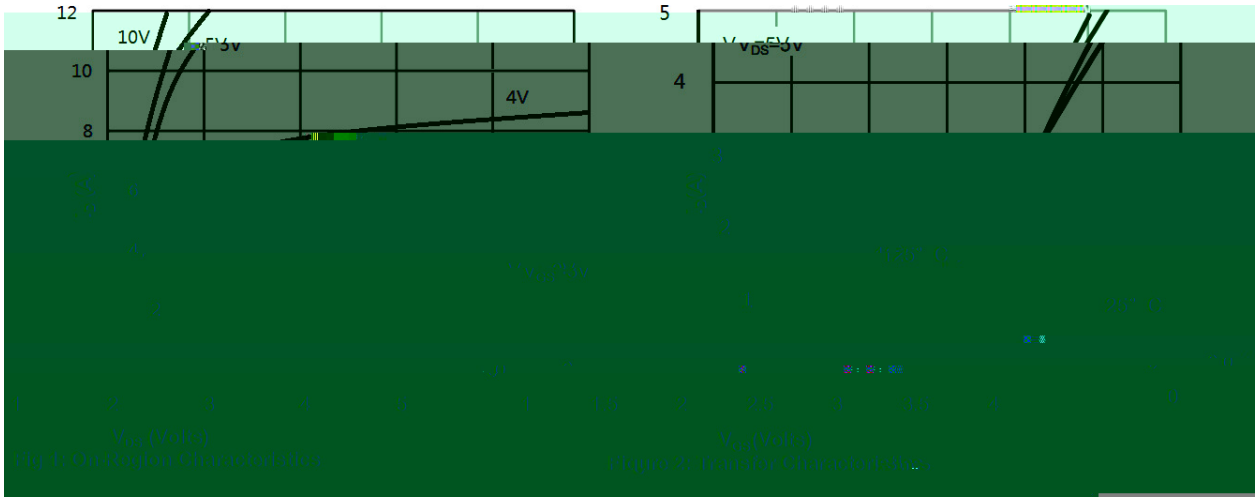


PIN1	G1	PIN 2	SN	PIN 3	G2
PIN 4	D2	PIN 5	SP	PIN 6	D1

See Marking Instructions.

Parameter	Symbol	Rating		Unit
		N-channe	P-channell	
Drain-Source Voltage	V_{DSS}	30	-30	V
Gate-Source Voltage	V_{GSS}	±20		V
Continuous Drain Current	I_D	2.7	-2.6	A
Pulsed Drain Current	I_{DM}	7	-7	A
Power Dissipation	P_D	1		W
Junction and Storage Temperature Range	T_J,T_{STG}	-55 to +150		
Maximum Junction-to-Ambient	$R_{\theta JA}$	125		

Parameter	Symbol	Test Conditions		Min	Typ	Max	Unit
Drain–Source Breakdown Voltage	BV_{DSS}	V_{GS}=0	I_D=250μA	30	31.5		V
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS}=0	V_{DS}=24V			1.0	μA
Gate–Body Leakage.	I_{GSS}	V_{GS}=±20V	V_{DS}=0V			±100	nA
Static Drain–Source On–Resistance	$R_{DS(on)1}$	V_{GS}=10V	I_D=2.0A		66	80	mΩ
	$R_{DS(on)2}$	V_{GS}=4.5V	I_D=1.0A		95	130	mΩ
Drain–Source Diode Forward Voltage	V_{SD}	V_{GS}=0V	I_D=1.0A			1.2	V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}	I_D=250μA	1.0	1.45	2.0	V
Input Capacitance	C_{iss}	V_{DS}=15V f=1.0MHz	V_{GS}=0V		200		pF
Output Capacitance	C_{oss}				30		pF
Reverse Transfer Capacitance	C_{rss}				20		pF
Total Gate Charge	Q_g	V_{GS}=10V, I_D=2A	V_{DS}=15V		5		nC
Gate Source Charge	Q_{gs}				0.8		
Gate Drain Charge	Q_{gd}				1.7		
Turn–On Delay Time	$t_{d(on)}$	V_{GS}=10V R_{GEN}=6Ω	V_{DS}=15V I_D=1A		4		ns
Turn–On Rise Time	t_r				11		
Turn–Off Delay Time	$t_{d(off)}$				9		
Turn–Off Fall Time	t_f				2.2		



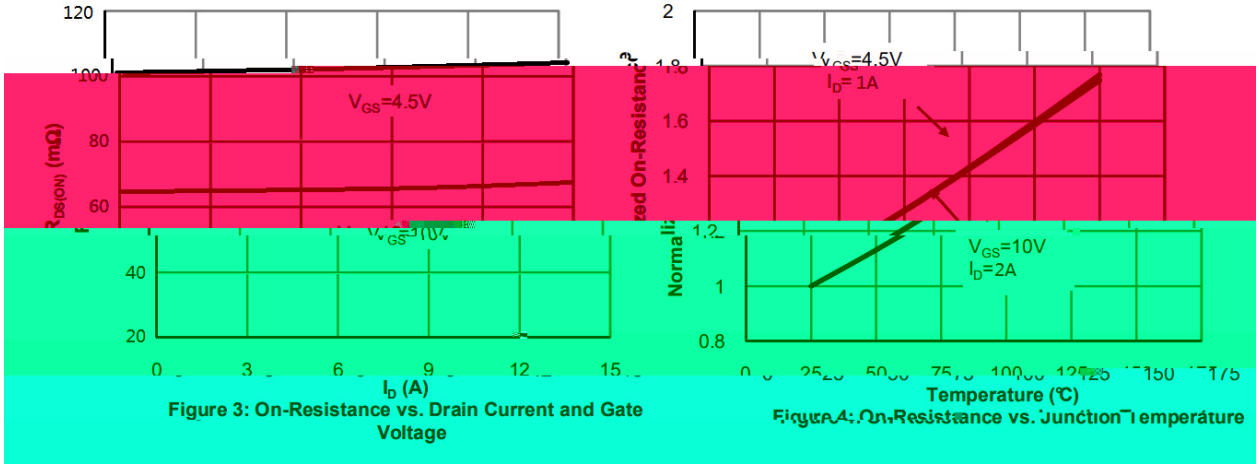
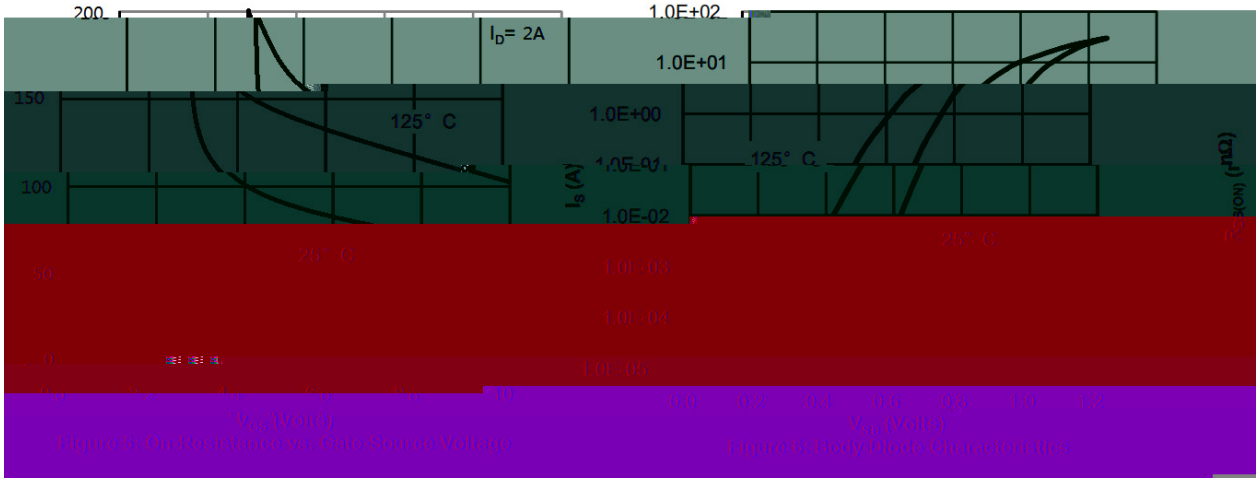


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

Figure 4: On-Resistance vs. Junction Temperature



Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain–Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V I_D=-250μA	-30	-31.5		V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS} I_D=-250μA	-0.5	-0.85	-2.0	V
Static Drain–Source On–Resistance	$R_{DS(on)}$	V_{GS}=-10V I_D=-2 A		75	95	mΩ
	$R_{DS(on)}$	V_{GS}=-4.5V I_D=-1.5A		88	150	mΩ
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-24V V_{GS}=0V			-1	μA
Gate–Body Leakage	I_{GSS}	V_{GS}=±20V V_{DS}=0V			±0.1	μA
Drain–Source Diode Forward Voltage	V_{SD}	I_S=-1.0A V_{GS}=0V			-1.2	V
Input Capacitance	C_{iss}	V_{DS}=-15V, V_{GS}=0V f=1MHz		250		pF
Output Capacitance	C_{oss}			50		
Reverse Transfer Capacitance	C_{rss}			40		
Total Gate Charge	Q_g	V_{DS}=-15V V_{GS}=-10V I_D=-2A		7.2		nC
Gate-to-Source Charge	Q_{gs}			1.1		
Gate-to-Drain Charge	Q_{gd}			1.6		
Turn–On Delay Time	$t_{d(on)}$	V_{DS}=-15V V_{GS}=-10V R_{GEN}=6Ω I_D=-2A		7.5		ns
Turn–On Rise Time	t_r			11.8		
Turn–Off Delay Time	$t_{d(off)}$			17		
Turn–Off Fall Time	t_f			6		

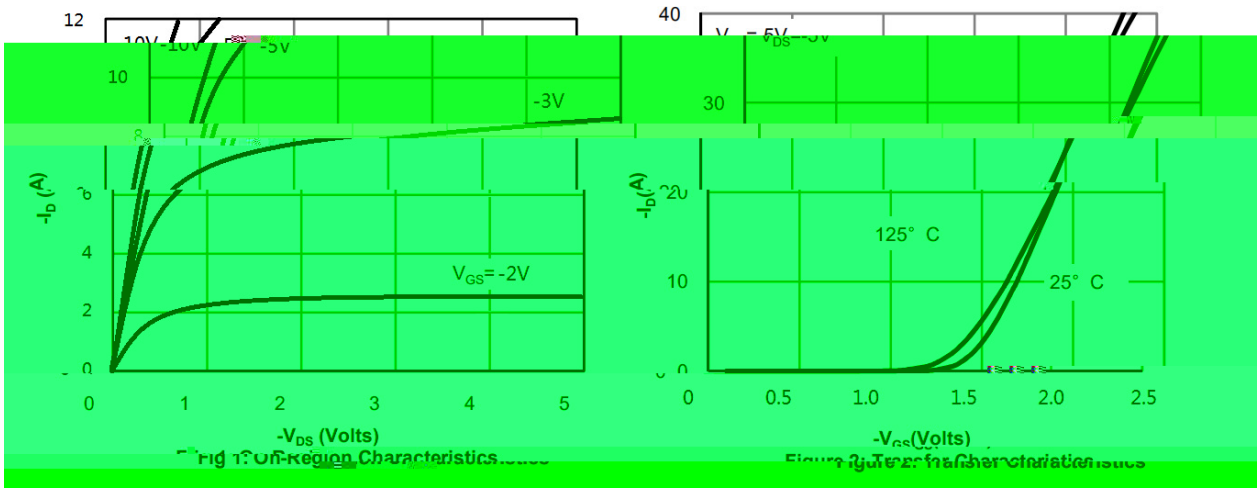


Fig 1: On-Region Characteristics

Figure 2: Transfer Characteristics

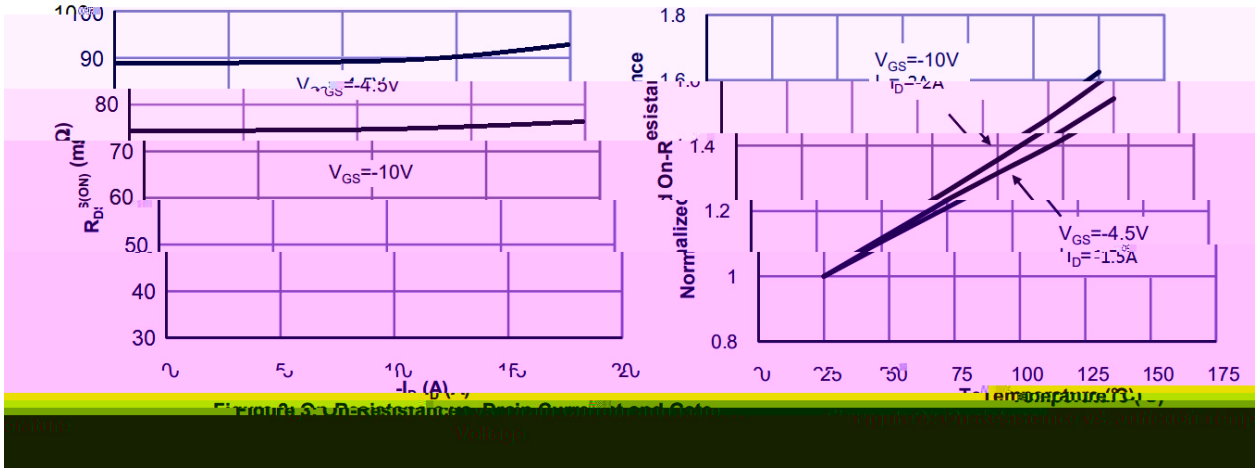


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

Figure 4: On-Resistance vs. Junction Temperature

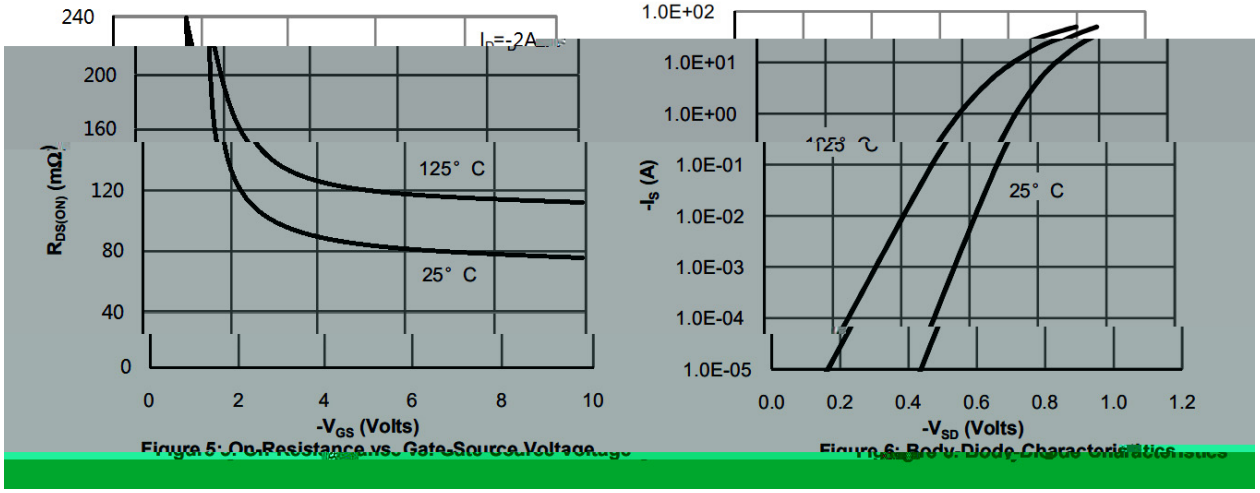
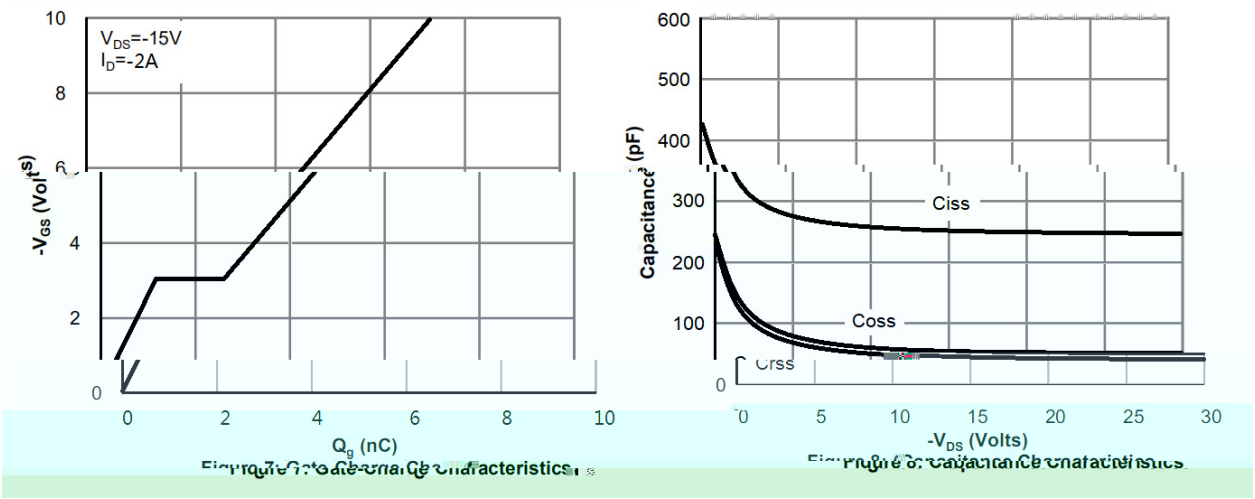
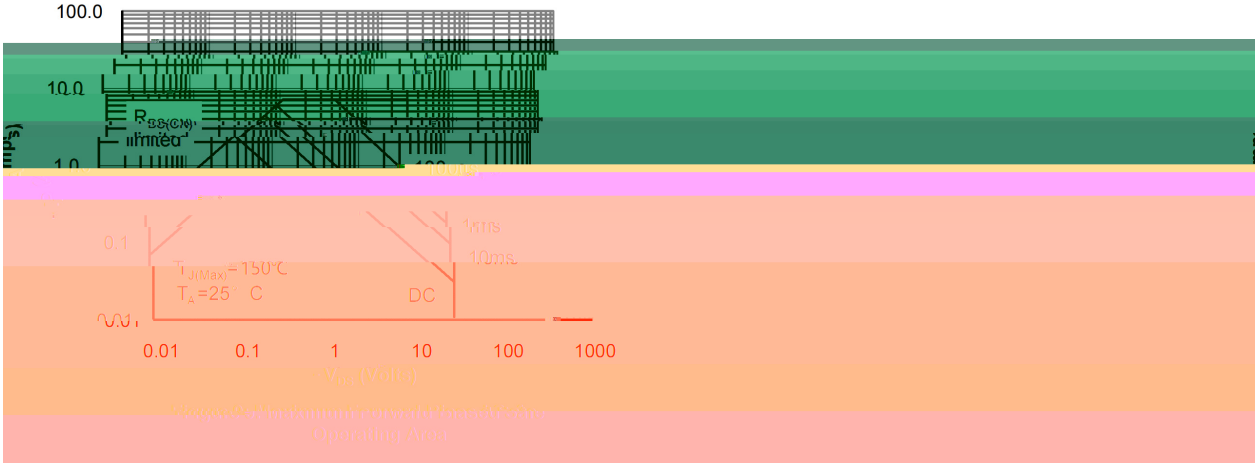
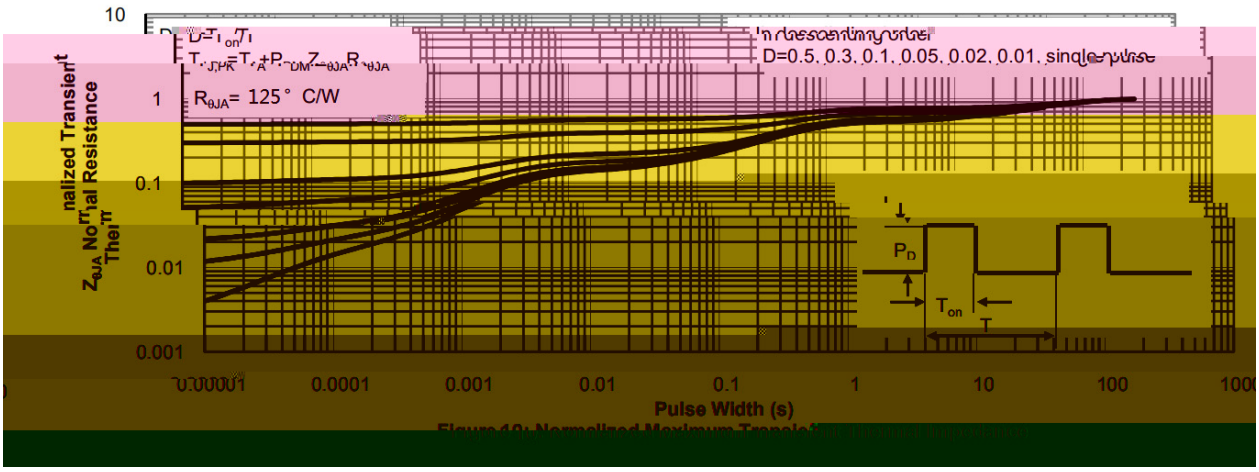


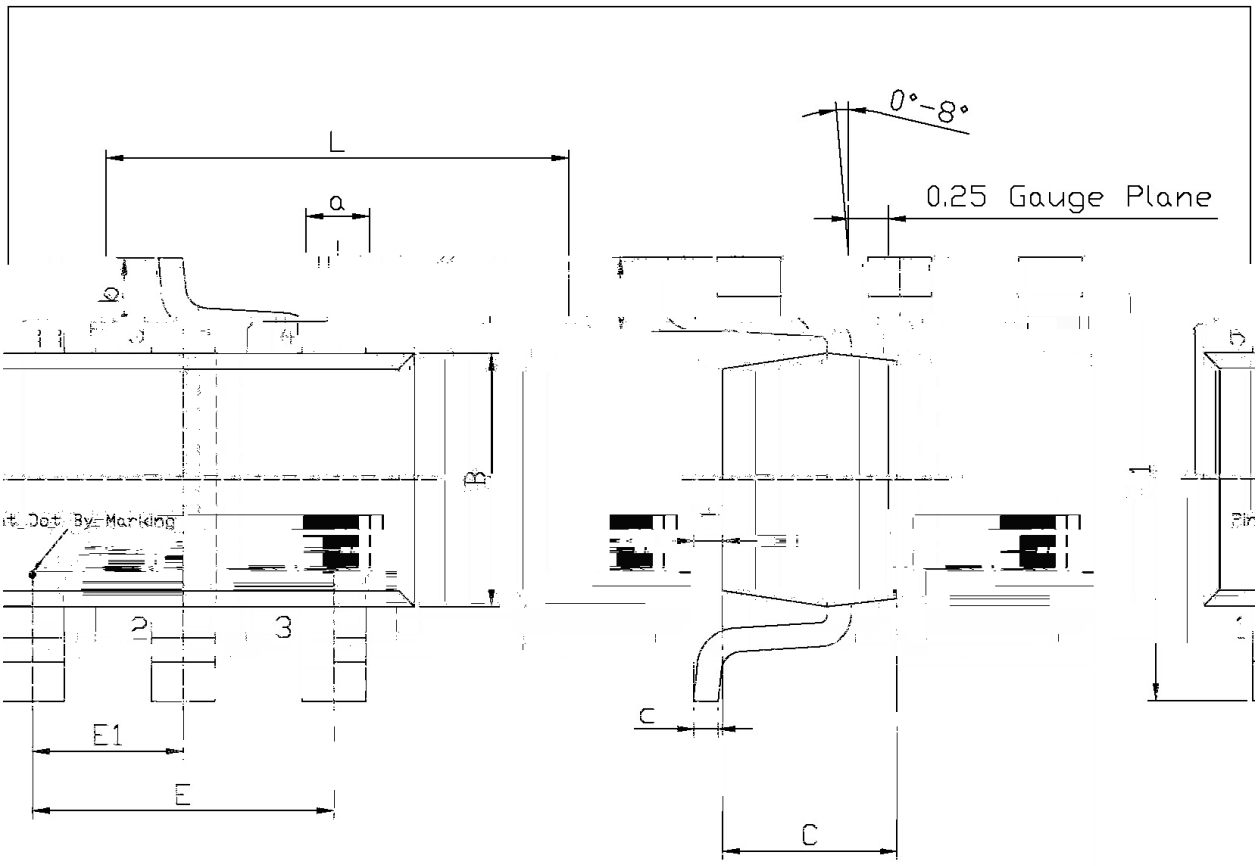
Figure 5: On-Resistance vs. Gate-Source Voltage

Figure 6: Body Diode Characteristics


V_{DS}=-15V
I_D=-2A
$-V_{GS}$ (Volts)
Q_g (nC)
Capacitance (pF)
Ciss
Coss
Crss
$-V_{DS}$ (Volts)


100.0
10.0
1.0
0.1
1ms
10ms
DC
$T_{J(Max)}$=150°C
T_A=25° C
0.01
0.1
1
10
100
1000

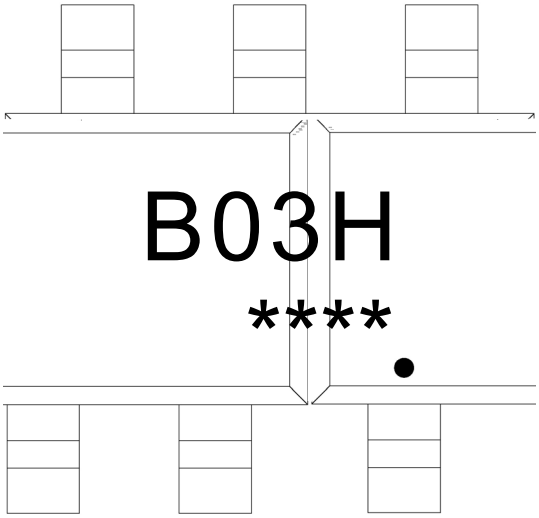

D=T_{on}/T
$T_{J,PK}$=T_A+P_{DM}*$Z_{\theta JA}$*$R_{\theta JA}$
$R_{\theta JA}$= 125 ° C/W
D=0.5, 0.3, 0.1, 0.05, 0.02, 0.01, single pulse
P_D
T_{on}
T
$Z_{\theta JA}$ Normalized Transient Thermal Resistance
Pulse Width (s)



Unit: mm

Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
L	2.82	3.02	E1	0.85	1.05
B	1.50	1.70	a	0.35	0.50
C	0.90	1.30	c	0.10	0.20
L1	2.60	3.00	b	0.35	0.55
E	1.80	2.00	F	0	0.15

SOT23-6

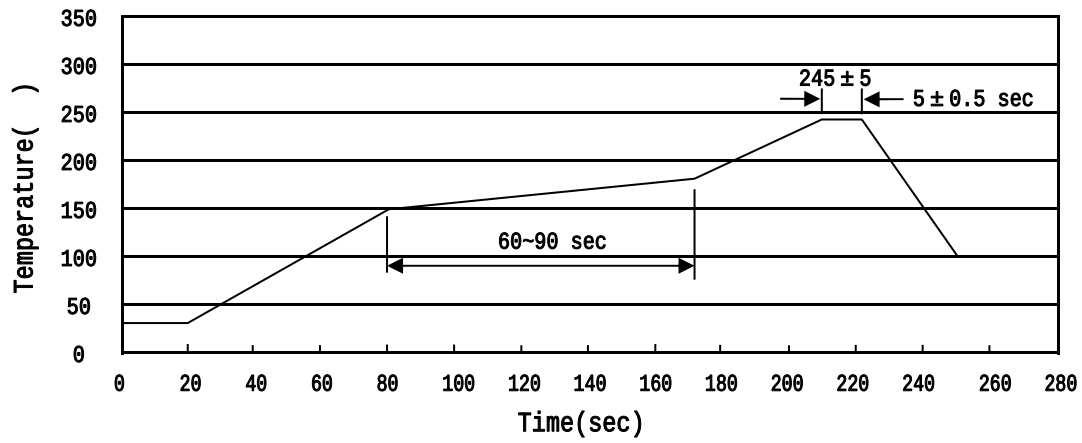


B03:

****:

Note:

B03	Product Type Code
H	Company Code
****:	Lot No.Code,code change with Lot No



Note:

1 150 180 60 90sec;

2 245 5 5 0.5sec;

3 2 10 /sec.

1.Preheating:150~180 , Time:60~90sec.

2.Peak Temp.:245 5 , Duration:5 0.5sec.

3. Cooling Speed: 2~10 /sec.

260 5 10 1 sec. Temp.:260±5 Time:10±1 sec

/ REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit：mm³)		
	只卷盘	卷盘盒	只盒	盒箱	只箱		盒	箱
SOT23-5/6	3,000	10	30,000	4	120,000	7 ×8	210×205×205	445×435×230